

# GaN Amplifier 50 V, 300 W 2.40 - 2.50 GHz



**MACOM PURE CARBIDE™**

**WST33H0NC**

Rev. V1

## Features

- MACOM PURE CARBIDE™ Amplifier Series
- Saturated Output Power = 300 W
- Output Power = 55 dBm
- Drain Efficiency = 75%
- Large Signal Gain = 17 dB
- CW Operation
- RoHS\* Compliant

## Applications

- Microwave Heating
- Industrial, Scientific, & Medical

## Description

The WST33H0NC is a 300 W packaged, partially-matched amplifier utilizing the high performance, 50 V, 0.25  $\mu\text{m}$  GaN on SiC production process. This amplifier operates from 2.40 G - 2.50 GHz and targets microwave heating applications.

Available in a thermally-enhanced, Cu-based package, the WST33H0NC provides superior performance under CW operation allowing customers to improve SWaP-C benchmarks in their next generation systems.

## Typical Performance CW:

- $V_{DS} = 50 \text{ V}$ ,  $I_{DQ} = 0 \text{ mA}$ ,  $V_{GS} = -4 \text{ V}$ ,  $T_C = 25^\circ\text{C}$

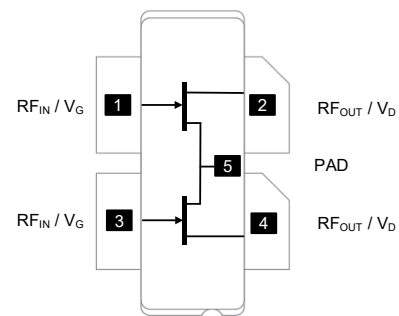
Frequency (GHz)	Output Power <sup>1</sup> (dBm)	Gain <sup>1</sup> (dB)	$\eta_D$ <sup>1</sup> (%)
2.40	56.0	18.0	75.8
2.45	55.4	17.4	76.7
2.50	54.8	16.8	77.3

1. Application board performance, Input power is 38 dBm, CW.



TO248

## Functional Schematic



## Pin Configuration

Pin #	Pin Name	Function
1, 3	RF <sub>IN</sub> / V <sub>G</sub>	RF Input / Gate
2, 4	RF <sub>OUT</sub> / V <sub>D</sub>	RF Output / Drain
5	Flange <sup>2</sup>	Ground / Source

2. The flange on the package bottom must be connected to RF, DC and thermal ground.

## Ordering Information

Part Number	Package
WST33H0NC-ASPPR	250 piece reel
WST33H0NC-SBPPR	Sample Board

1 \* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

# GaN Amplifier 50 V, 300 W

## 2.40 - 2.50 GHz



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**RF Electrical Characteristics:  $T_C = 25^\circ\text{C}$ ,  $V_{DS} = 50\text{ V}$ ,  $I_{DQ} = 0\text{ mA}$ ,  $V_{GS} = -4\text{ V}$**

**Note: Performance in MACOM 2.40 - 2.50 GHz Evaluation Test Fixture, 50  $\Omega$  system**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Output Power	CW, 2.45 GHz, $P_{IN} = 38\text{ dBm}$	$P_{SAT}$	-	55.4	-	dBm
Large Signal Gain	CW, 2.45 GHz, $P_{IN} = 38\text{ dBm}$	$G_{SAT}$	-	17.4	-	dB
Drain Efficiency	CW, 2.45 GHz, $P_{IN} = 38\text{ dBm}$	$\eta_{SAT}$	-	76.7	-	%
Large Signal S11	CW, 2.45 GHz, $P_{IN} = 38\text{ dBm}$	$L_{SS11}$	-	-18.0	-	dB
Ruggedness: Output Mismatch	Pulsed <sup>3</sup> , All phase angles	$\Psi$	VSWR = 20:1, No Damage			

3. Pulse Details: 100  $\mu\text{s}$ , 10 % duty cycle.

**RF Electrical Specifications<sup>4</sup>:  $T_A = 25^\circ\text{C}$ ,  $V_{DS} = 50\text{ V}$ ,  $I_{DQ} = 0\text{ mA}$ ,  $V_{GS} = -4\text{ V}$**

**Note: Performance in MACOM Production Test Fixture, 50  $\Omega$  system**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Saturated Drain Efficiency	Pulsed <sup>5</sup> , 2.40 GHz, $P_{IN} 40.5\text{ dBm}$	$\eta_{SAT}$	-	52.7	-	dBm
Saturated Output Power	Pulsed <sup>5</sup> , 2.40 GHz, $P_{IN} 40.5\text{ dBm}$	$P_{SAT}$	-	63.1	-	%

4. Test and screening under class-C operation for peak efficiency. User may operate under different operating class depending on specific system requirements.

5. Pulse Details: 100  $\mu\text{s}$  pulse width, 10 % duty cycle.

**DC Electrical Characteristics:  $T_A = 25^\circ\text{C}$**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Drain-Source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 10\text{ V}$	$I_{DLK}$	-	-	3.6	mA
Gate-Source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 10\text{ V}$	$I_{GLK}$	-	-	3.6	mA
Gate Pinch-Off Voltage	$V_{DS} = 10\text{ V}$ , $I_{DS} = 25.6\text{ mA}$	$V_{P10}$	-3.5	-	-1.9	V
Gate Resistance	-	-	50	-	-	k $\Omega$

### Absolute Maximum Ratings <sup>6,7</sup>

Parameter	Absolute Maximum
Drain Source Voltage, $V_{DS}$	150 V
Gate Source Voltage, $V_{GS}$	-8 to +2 V
Drain Current, $I_D$	49 A
Gate Current, $I_G$	51.2 mA
Gate Input Power	42 dBm
Storage Temperature Range	-65°C to +150°C
Case Operating Temperature Range	-40°C to +85°C
Absolute Maximum Channel Temperature	+275°C, MTTF > 1E6

6. Exceeding any one or combination of these limits may cause permanent damage to this device.  
7. MACOM does not recommend sustained operation above maximum operating conditions.

### Thermal Characteristics <sup>8</sup>

Parameter	Test Conditions	Symbol	Typical	Units
Thermal Resistance using Finite Element Analysis	$V_{DS} = 50 \text{ V}$ , $P_{DISS} = 144 \text{ W}$ , $T_C = 85^\circ\text{C}$	$R_{\theta}(\text{FEA})$	0.62	°C/W
Thermal Resistance using Infrared Measurement of Die Surface Temperature	$V_{DS} = 50 \text{ V}$ , $P_{DISS} = 205 \text{ W}$ , $T_C = 85^\circ\text{C}$	$R_{\theta}(\text{IR})$	0.68	°C/W

8. Case temperature measured using thermocouple embedded in heat-sink. Contact local applications support team for more details on this measurement.

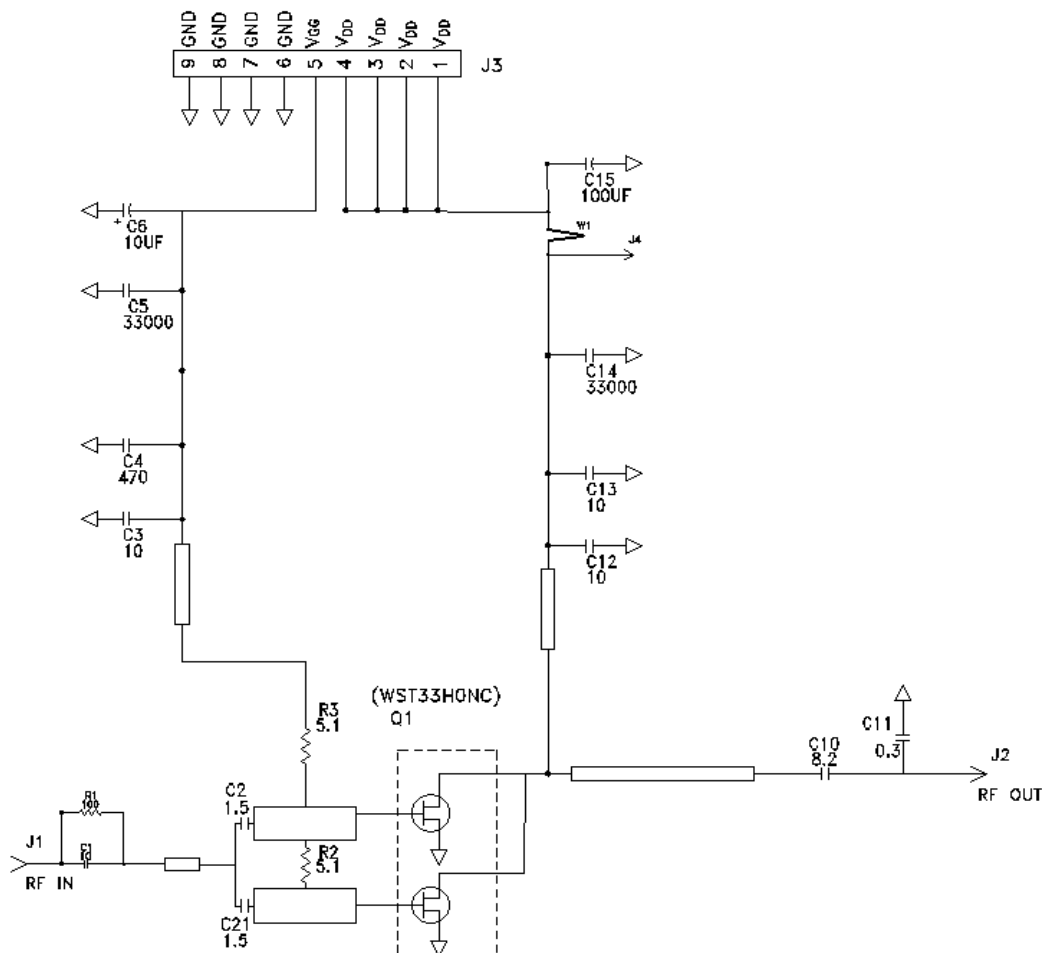
### Handling Procedures

Please observe the following precautions to avoid damage:

### Static Sensitivity

Gallium Nitride Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

Evaluation Test Fixture and Recommended Tuning Solution 2.40 - 2.50 GHz



**Description**

Parts measured on evaluation board (20-mil thick RO6035 HTC). Matching is provided using a combination of lumped elements and transmission lines as shown in the simplified schematic above. Recommended tuning solution component placement, transmission lines, and details are shown on the next page.

**Bias Sequencing\***

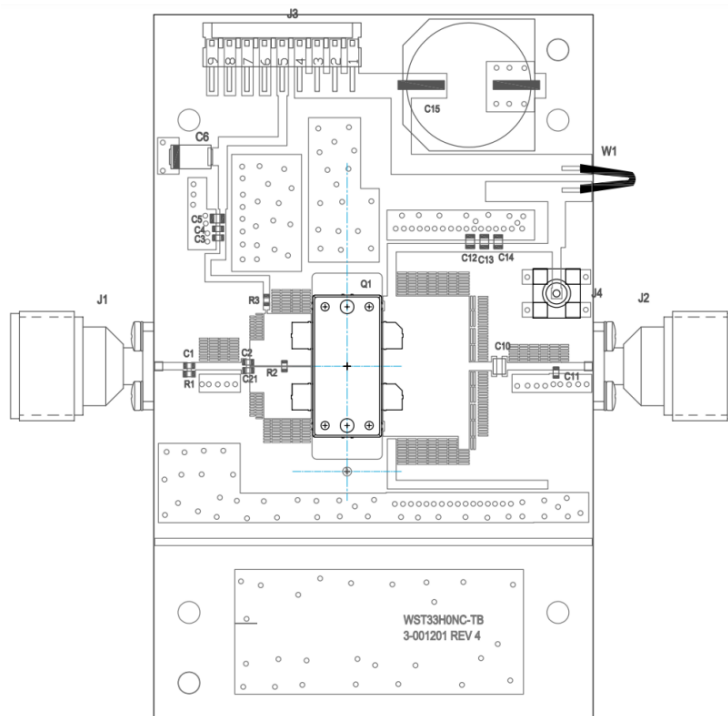
**Turning the device ON**

1. Set  $V_{GS}$  to pinch-off ( $V_P = -4$  V).
2. Turn on  $V_{DS}$  to nominal voltage (50 V).
3. (This device biased in class C, so no need to adjust  $V_{GS}$ )
4. Apply RF power to desired level.

**Turning the device OFF**

1. Turn the RF power OFF.
2. Decrease  $V_{DS}$  down to 0 V.
3. Turn off  $V_{GS}$ .

**Evaluation Test Fixture and Recommended Tuning Solution 2.40 - 2.50 GHz**



Reference Designator	Value	Tolerance	Manufacturer	Part Number
C1,C3	10 pF	± 5 %	ATC	600S100JW250XT
C2,C21	1.5 pF	± 0.1 pF	ATC	ATC600S1R5BT250T
C10	8.2 pF	± 5 %	ATC	800R8R2JT500XT1K
C11	0.3 pF	± 0.05 pF	ATC	600S0R3AT250XT
C12,C13	10 pF	± 1 %	ATC	600F100FT250XT
C5,C14	33000 pF	± 10 %	Murata	GRM21BR72A333KA01
C15	100 µF	± 20 %	Panasonic	EEVEB2C101M
C4	470 pF	± 5 %	AVX	06031C471JAT2A
C6	10 µF	± 10 %	AVX	TAJC106K016RNJ
R3,R2	5.1 Ω	± 1 %	Vishay	CRCW06035R10FNEA
R1	100 Ω	± 1 %	Vishay	CRCW0603100RFKEA
W1	18 AWG		BNTECHGO	UPC 74227160
J1,J2			Huber-Shuner	23N-50-31
J4			Cinch	131-3711-201
J3			TE Connectivity	640457-9
Q1	MACOM GaN Power Amplifier			WST33H0NC
PCB	RO6035 HTC, 20 mil, 2 oz. Cu, Tin/Lead Finish			

# GaN Amplifier 50 V, 300 W

## 2.40 - 2.50 GHz



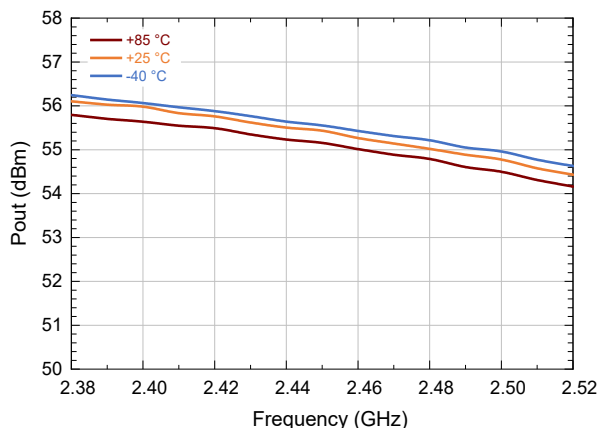
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**WST33H0NC**

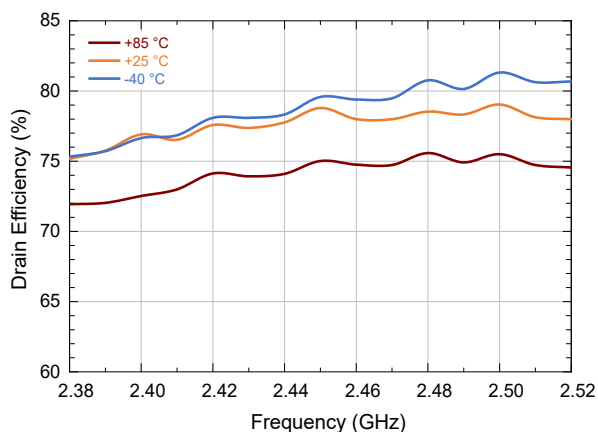
Rev. V1

**Typical Performance Curves: Large Signal Performance vs. Temperature**  
 CW,  $V_D = 50$  V,  $P_{IN} = 38$  dBm,  $V_G = -4$  V,  $T_B = 25^\circ\text{C}$  (Unless Otherwise Noted)

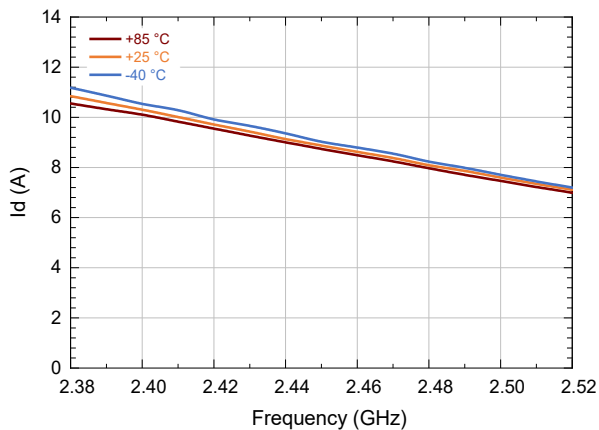
**Output Power**



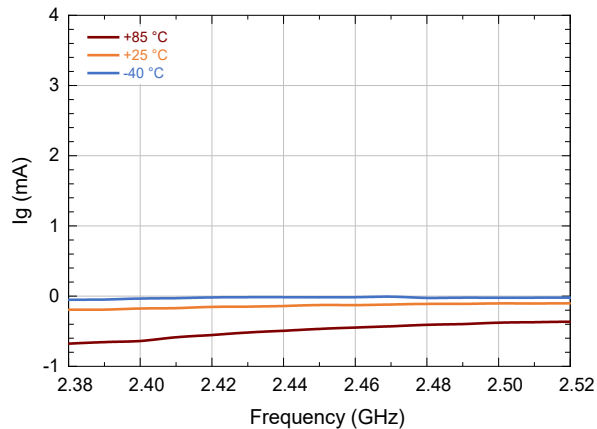
**Drain Efficiency**



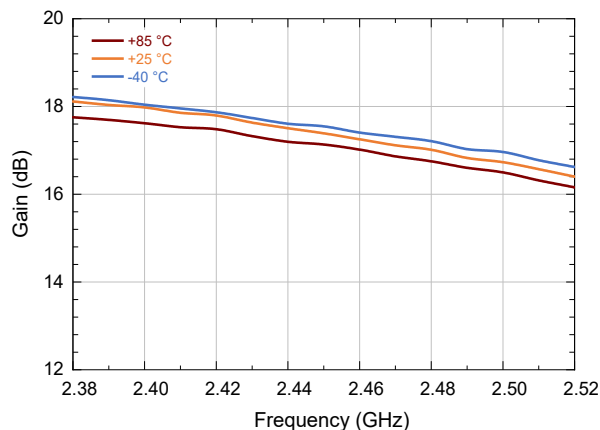
**Drain Current**



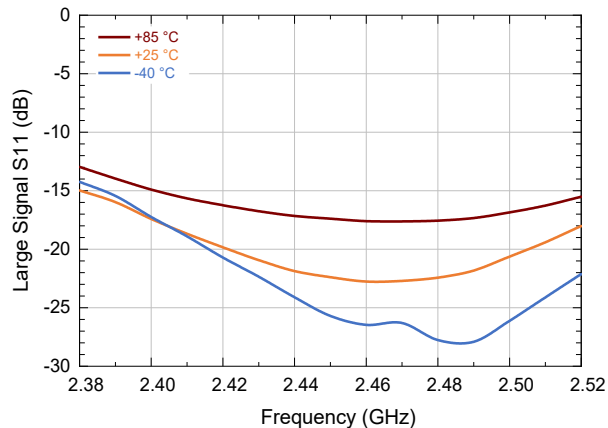
**Gate Current**



**Large Signal Gain**



**Large Signal S11**



# GaN Amplifier 50 V, 300 W

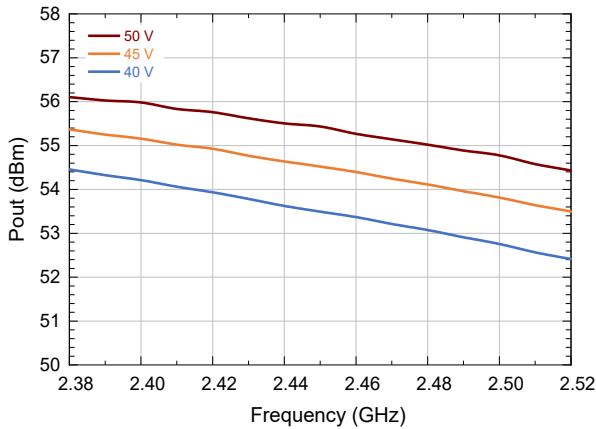
## 2.40 - 2.50 GHz



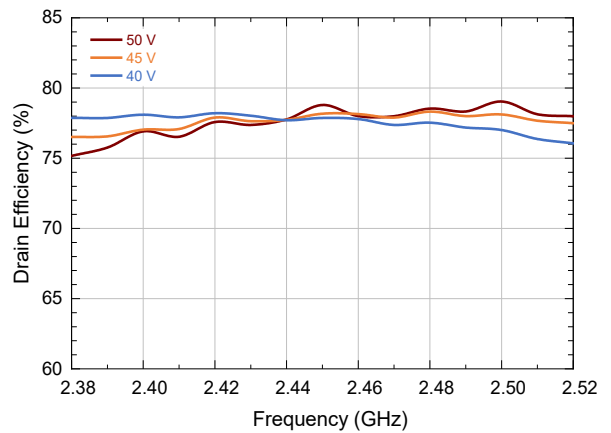
### Typical Performance Curves: Large Signal Performance vs. Drain Voltage

CW,  $P_{IN} = 38$  dBm,  $V_G = -4$  V,  $T_B = 25^\circ\text{C}$

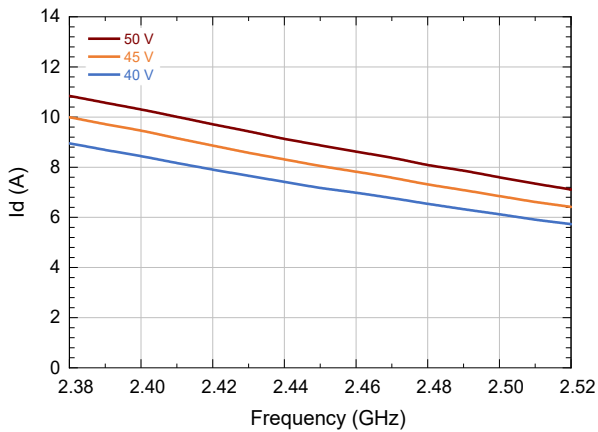
**Output Power**



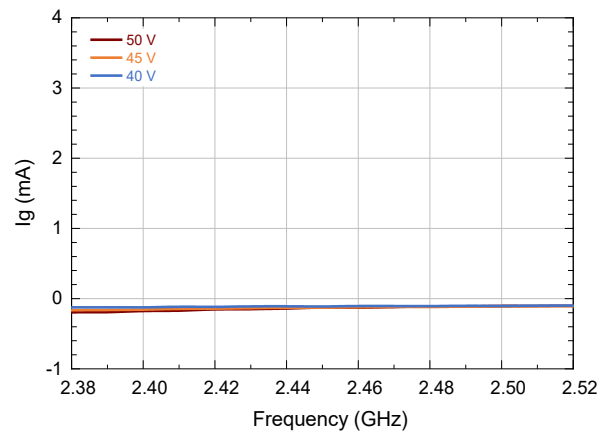
**Drain Efficiency**



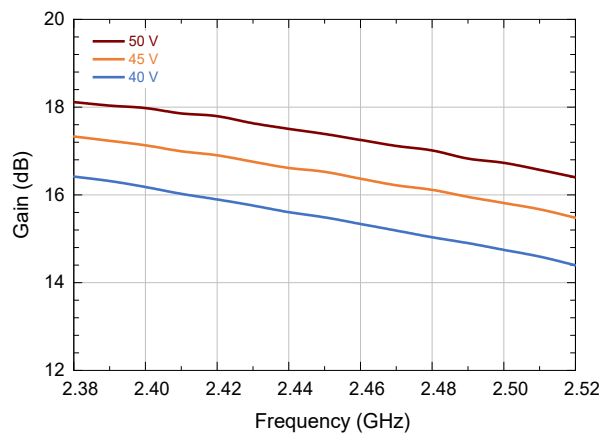
**Drain Current**



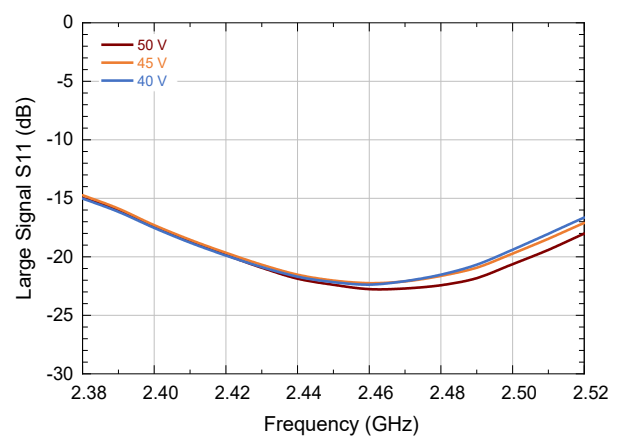
**Gate Current**



**Large Signal Gain**



**Large Signal S11**



# GaN Amplifier 50 V, 300 W 2.40 - 2.50 GHz



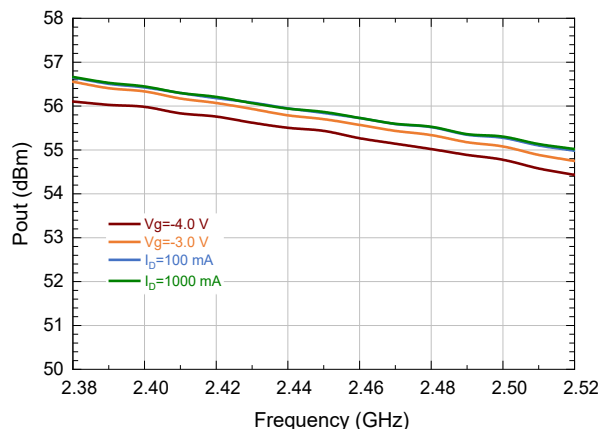
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**WST33H0NC**

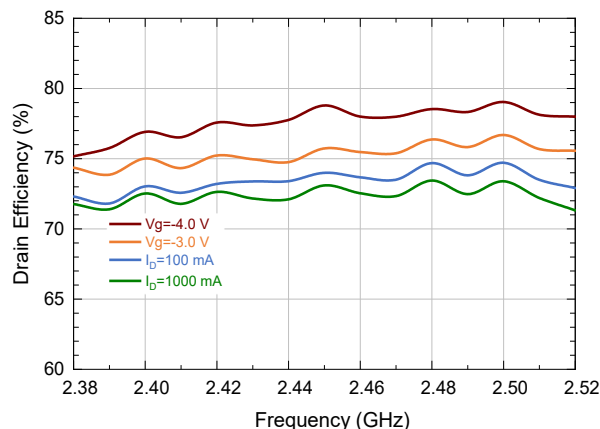
Rev. V1

## Typical Performance Curves: Large Signal Performance vs. Quiescent Drain Current CW, $V_D = 50\text{ V}$ , $P_{IN} = 38\text{ dBm}$ , $T_B = 25^\circ\text{C}$

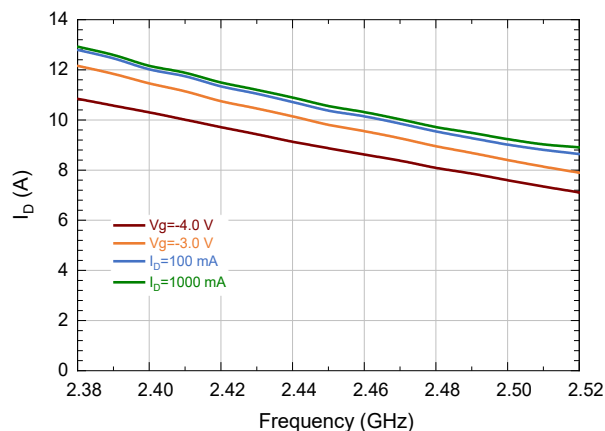
**Output Power**



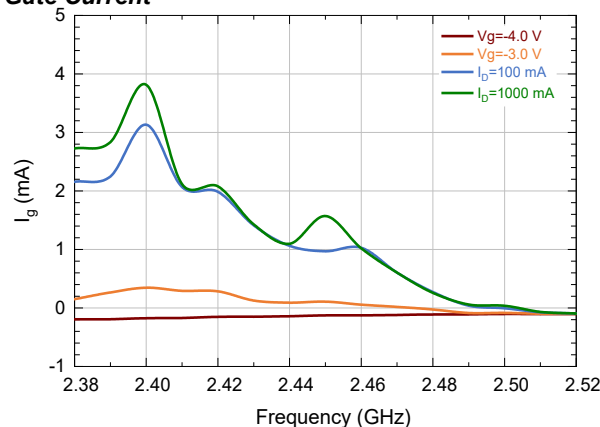
**Drain Efficiency**



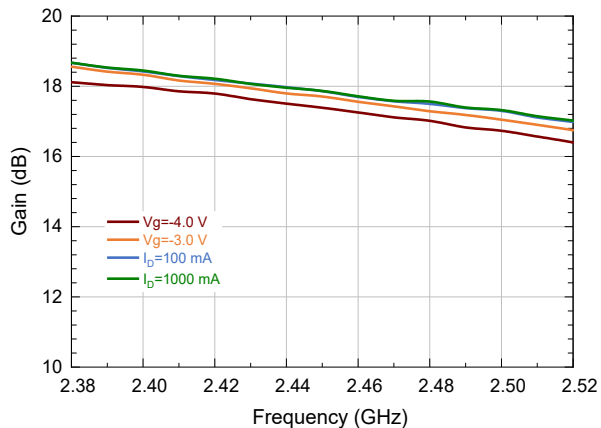
**Drain Current**



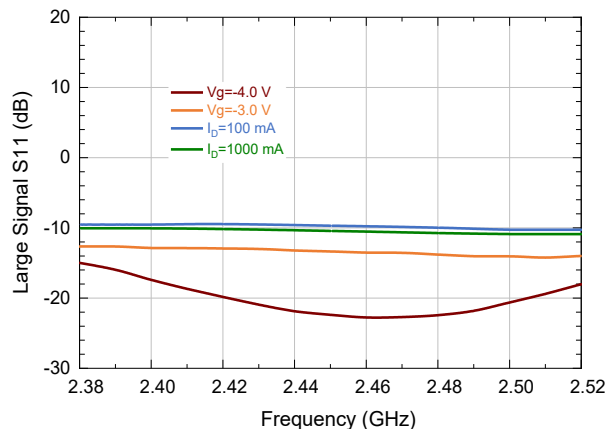
**Gate Current**



**Large Signal Gain**



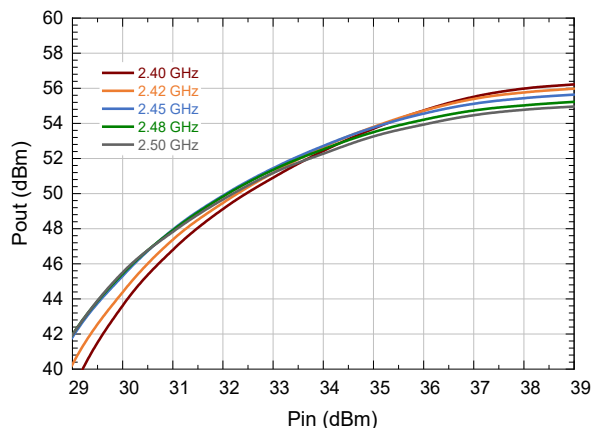
**Large Signal S11**



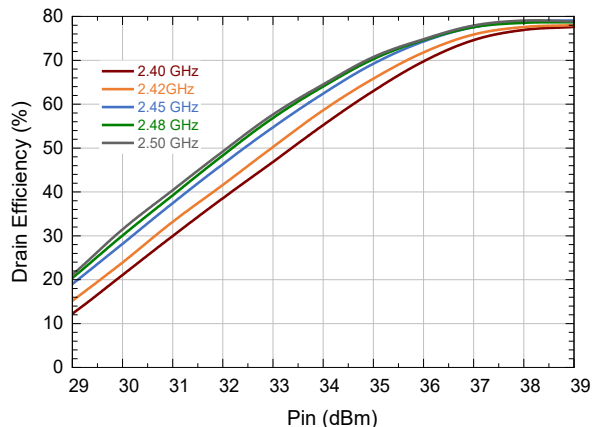


Typical Performance Curves: Drive-Up vs. Frequency  
CW,  $V_D = 50\text{ V}$ ,  $V_G = -4\text{ V}$ ,  $T_B = 25^\circ\text{C}$

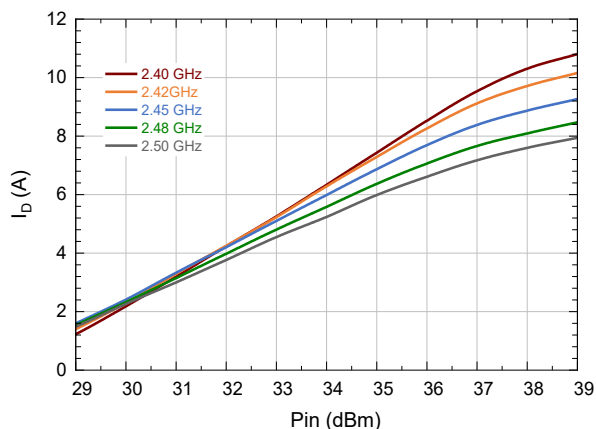
Output Power



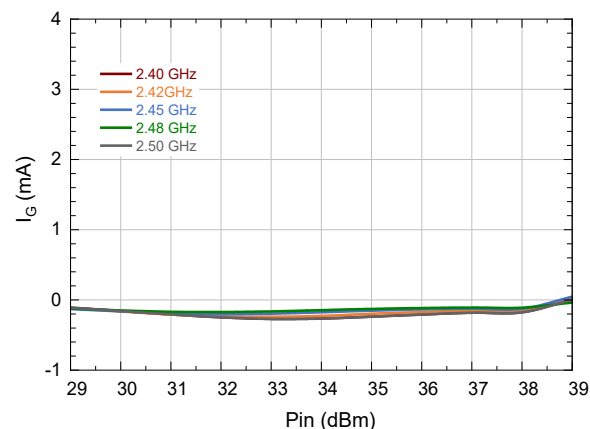
Drain Efficiency



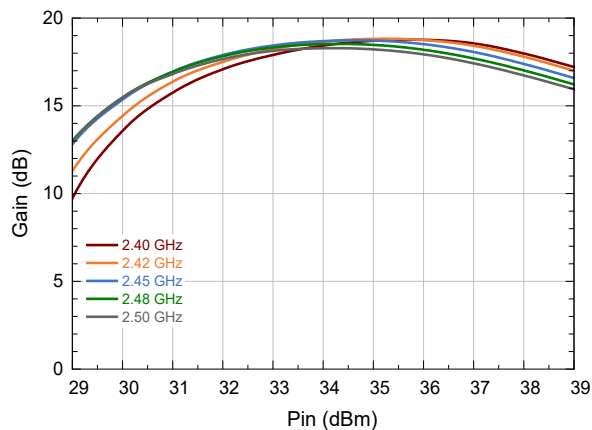
Drain Current



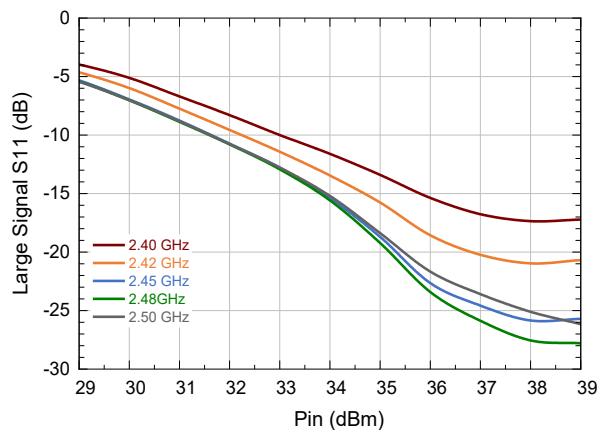
Gate Current



Gain

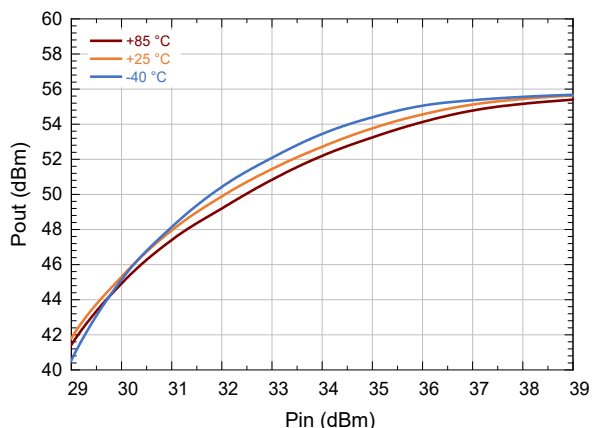


Large Signal S11

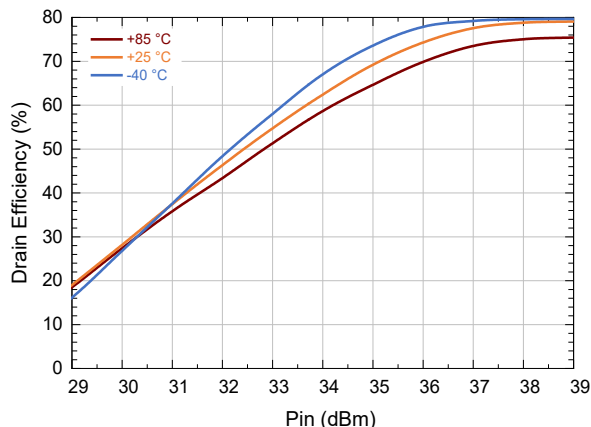


**Typical Performance Curves: Drive-Up vs. Temperature**  
CW,  $V_D = 50$  V, Freq. = 2.45 GHz,  $V_G = -4$  V

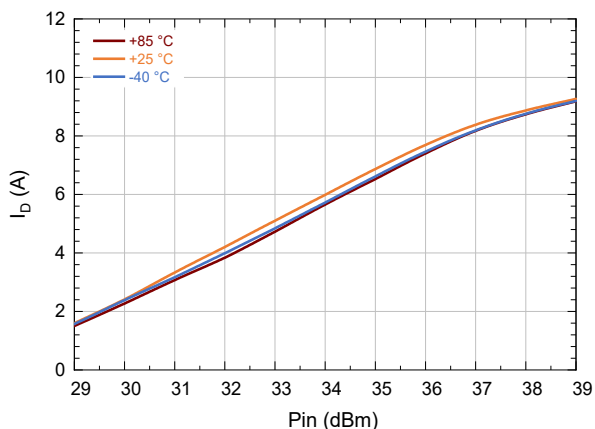
**Output Power**



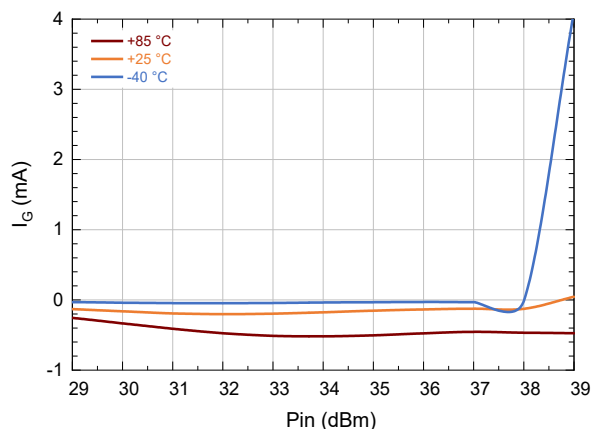
**Drain Efficiency**



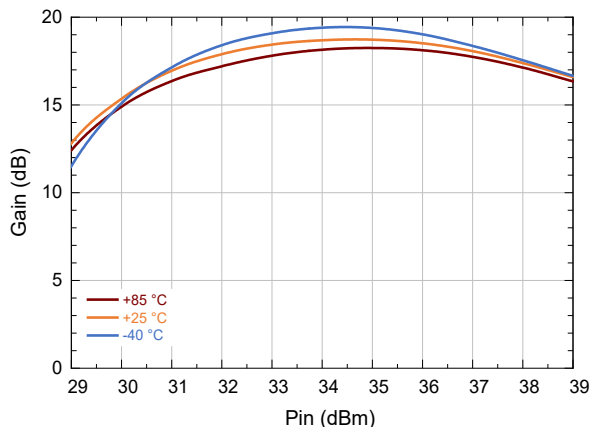
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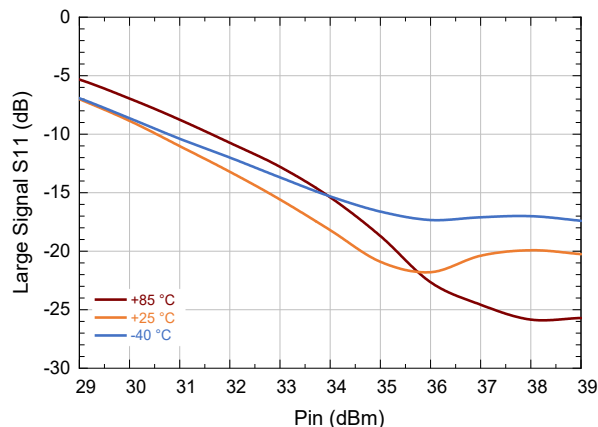
**Gate Current**



**Gain**

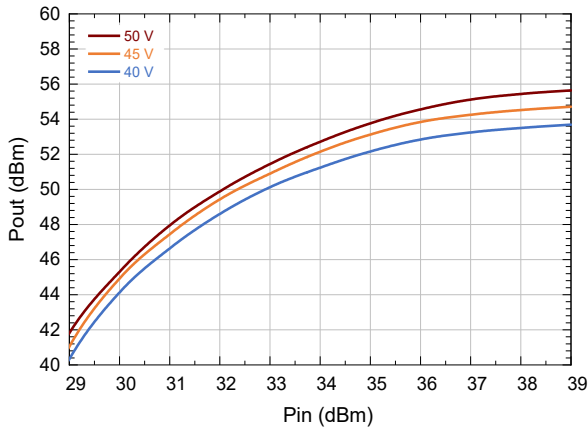


**Large Signal S11**

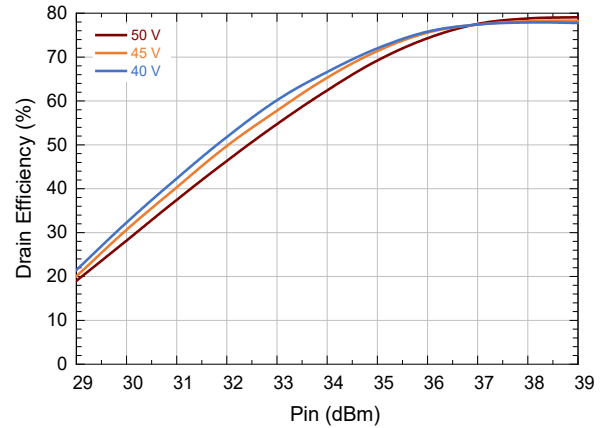


Typical Performance Curves: Drive-Up vs. Drain Voltage  
CW, Freq. = 2.45 GHz,  $V_G = -4$  V,  $T_B = 25^\circ\text{C}$

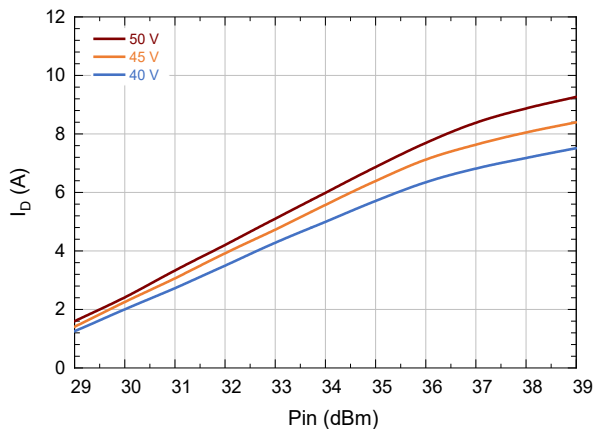
Output Power



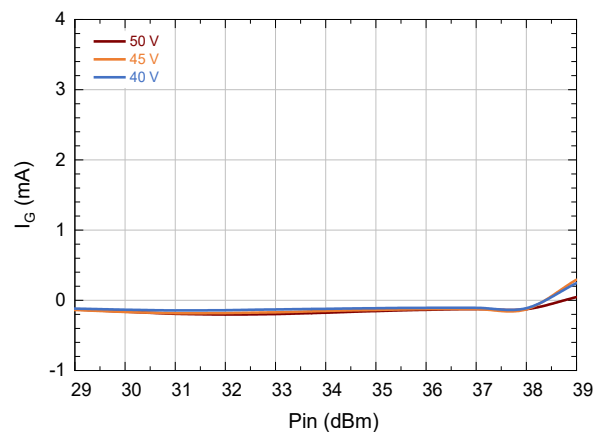
Drain Efficiency



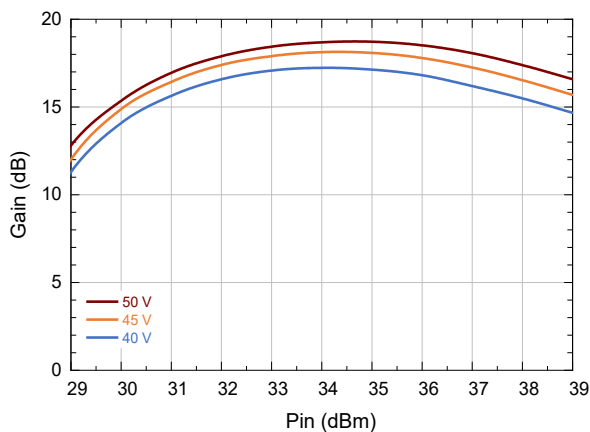
Drain Current



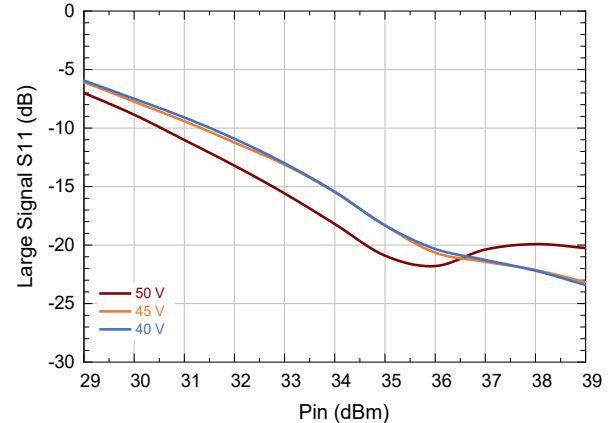
Gate Current



Gain

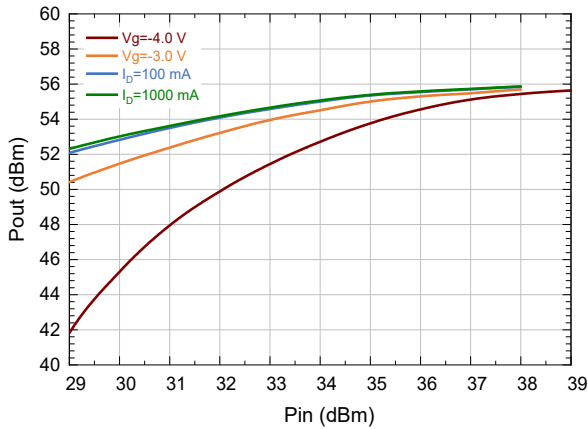


Large Signal S11

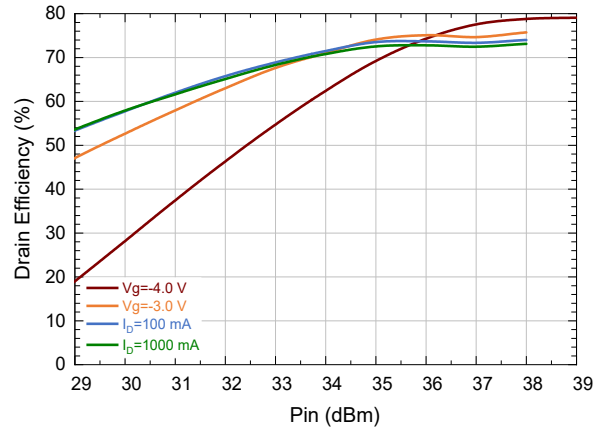


Typical Performance Curves: Drive-Up vs. Quiescent Drain Current  
CW,  $V_D = 50$  V, Freq. = 2.45 GHz,  $T_B = 25^\circ\text{C}$

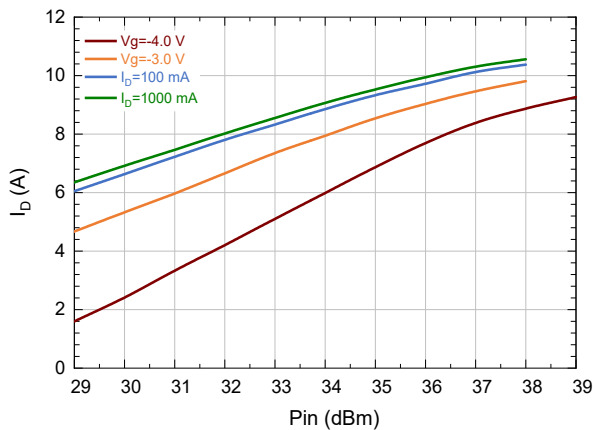
Output Power



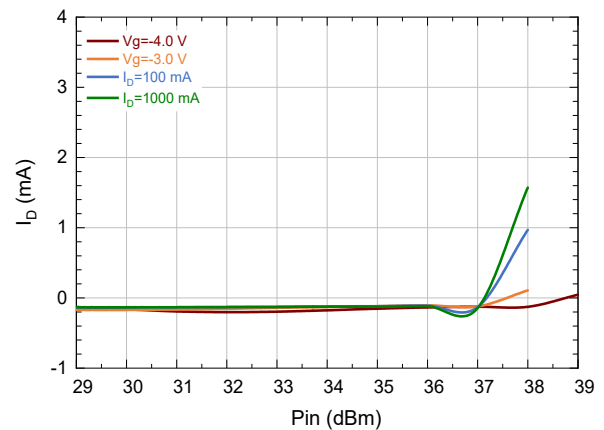
Drain Efficiency



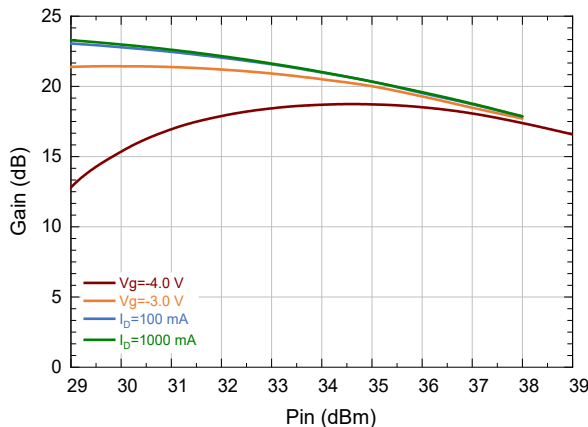
Drain Current



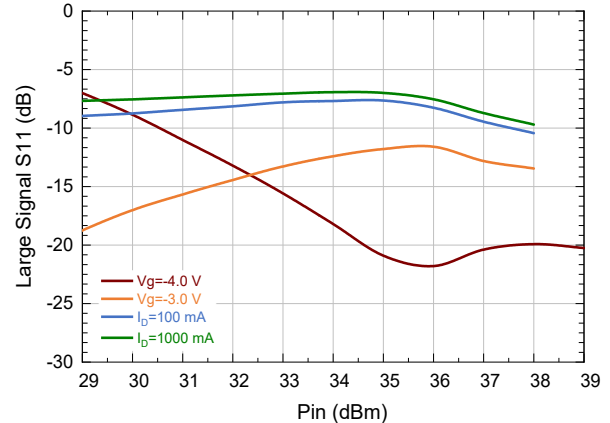
Gate Current



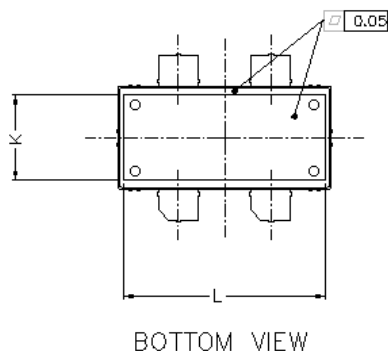
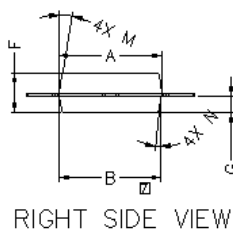
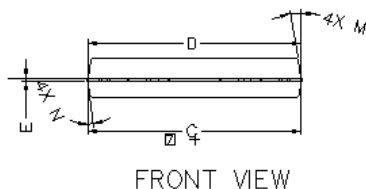
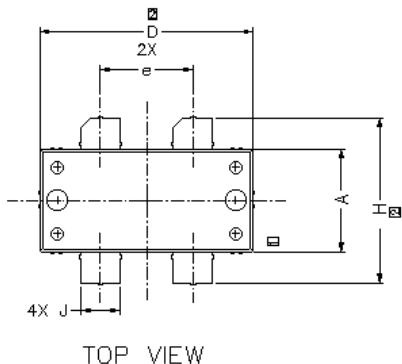
Gain



Large Signal S11



**Lead-Free Outline Drawing<sup>†</sup>**



Remarks:

1. Interpret dimensions and tolerances per ASME Y14.5M-1994
2. Mold/Dam Bar/Metal protrusion of 0.30mm max per side not included.
3. Metal protrusions are connected to source and shall not exceed 0.10mm max.
4. Fillets and radii:-  
Unless otherwise noted all radii are 0.30mm max.
5. Molded package Ra 1.2-1.6um.
6. All metal surfaces are tin plated, except area of cut.
7. Does not include Mold/Dam Bar and Metal protrusion.

Dim.	Inches			Millimeters		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.390	0.392	0.394	9.91	9.96	10.01
B	0.383	0.385	0.387	9.73	9.78	9.83
C	0.808	0.810	0.812	20.52	20.57	20.62
D	0.808	0.810	0.812	20.52	20.57	20.62
E	0.007	0.010	0.013	0.17	0.25	0.33
F	0.148	0.150	0.152	3.76	3.81	3.86
G	0.060	0.062	0.064	1.52	1.57	1.62
H	0.624	0.628	0.632	15.86	15.96	16.06
J	0.148	0.150	0.152	3.76	3.81	3.86
K	—	0.325	—	—	8.25	—
L	—	0.764	—	—	19.4	—
M	—	10°±1°	—	—	10°±1°	—
N	—	7°±1°	—	—	7°±1°	—
e	—	0.350	—	—	8.89	—

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